Unit: mm

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

# SSM3K7002FU

High Speed Switching Applications Analog Switch Applications

• Small package

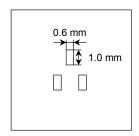
• Low ON resistance :  $R_{on} = 3.3 \Omega \text{ (max) } (@V_{GS} = 4.5 \text{ V})$ 

:  $R_{on} = 3.2 \Omega \text{ (max) (@V_{GS} = 5 V)}$ :  $R_{on} = 3.0 \Omega \text{ (max) (@V_{GS} = 10 V)}$ 

### Maximum Ratings (Ta = 25°C)

| Characteristics                     |       | Symbol                | Rating  | Unit |  |
|-------------------------------------|-------|-----------------------|---------|------|--|
| Drain-Source voltage                |       | V <sub>DS</sub>       | 60      | V    |  |
| Gate-Source voltage                 |       | $V_{GSS}$             | ± 20    | V    |  |
| Drain current                       | DC    | I <sub>D</sub>        | 200     | mA   |  |
|                                     | Pulse | I <sub>DP</sub>       | 800     |      |  |
| Drain power dissipation (Ta = 25°C) |       | P <sub>D</sub> (Note) | 150     | mW   |  |
| Channel temperature                 |       | T <sub>ch</sub>       | 150     | °C   |  |
| Storage temperature range           |       | T <sub>stg</sub>      | -55~150 | °C   |  |

Note: mounted on FR4 board (25.4 mm  $\times$  25.4 mm  $\times$  1.6 t, Cu Pad: 0.6mm<sup>2</sup>  $\times$  3)



### 2.1± 0.1 1.25± 0.1 1.25± 0.1 1.25± 0.1 1.25± 0.1 1.25± 0.1 1.25± 0.1 1.25± 0.1

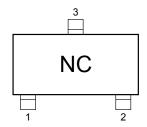
1.GATE 2.SOURCE

3.DRAIN

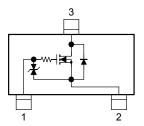
# JEDEC — JEITA SC-70 TOSHIBA 2-2E1E

USM

#### Marking



## **Equivalent Circuit (top view)**



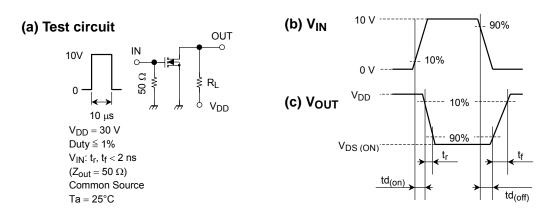
### **Handling Precaution**

When handling individual devices (which are not yet mounting on a circuit board), be sure that the environment is protected against electrostatic electricity. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.

#### **Electrical Characteristics (Ta = 25°C)**

| Characteristics                |                     | Symbol               | Test Condition   | Min | Тур | Max  | Unit |
|--------------------------------|---------------------|----------------------|--|-----|-----|------|------|
| Gate leakage current           |                     | I <sub>GSS</sub>     | $V_{GS} = \pm 20 \text{ V}, V_{DS} = 0$                | _   | _   | ± 10 | μА   |
| Drain-Source breakdown voltage |                     | V (BR) DSS           | $I_D = 0.1 \text{ mA}, V_{GS} = 0$                     | 60  | _   | _    | V    |
| Drain cut-off current          |                     | I <sub>DSS</sub>     | V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0            | _   | _   | 1    | μА   |
| Gate threshold voltage         |                     | V <sub>th</sub>      | $V_{DS} = 10 \text{ V}, I_D = 0.25 \text{ mA}$         | 1.0 | _   | 2.5  | V    |
| Forward transfer admittance    |                     | Y <sub>fs</sub>      | $V_{DS} = 10 \text{ V}, I_D = 200 \text{ mA}$          | 170 | _   | _    | mS   |
| Drain-Source ON resistance     |                     | R <sub>DS (ON)</sub> | $I_D = 500 \text{ mA}, V_{GS} = 10 \text{ V}$          | _   | 2.0 | 3.0  | Ω    |
|                                |                     |                      | $I_D = 100 \text{ mA}, V_{GS} = 5 \text{ V}$           | _   | 2.1 | 3.2  |      |
|                                |                     |                      | $I_D = 100 \text{ mA}, V_{GS} = 4.5 \text{ V}$         | _   | 2.2 | 3.3  |      |
| Input capacitance              |                     | C <sub>iss</sub>     |  | _   | 17  | _    | pF   |
| Reverse transfer capacitance   |                     | C <sub>rss</sub>     | $V_{DS} = 25 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$ | _   | 1.4 | _    | pF   |
| Output capacitance             |                     | C <sub>oss</sub>     |  |     | 5.8 | _    | pF   |
| Switching time                 | Turn-on delay time  | td <sub>(on)</sub>   | $V_{DD} = 30V$ , $I_D = 200$ mA,                       |     | 2.4 | 4.0  | ns   |
|                                | Turn-off delay time | td <sub>(off)</sub>  | V <sub>GS</sub> = 0 ~ 10V                              | _   | 26  | 40   |      |

### **Switching Time Test Circuit**



#### **Precaution**

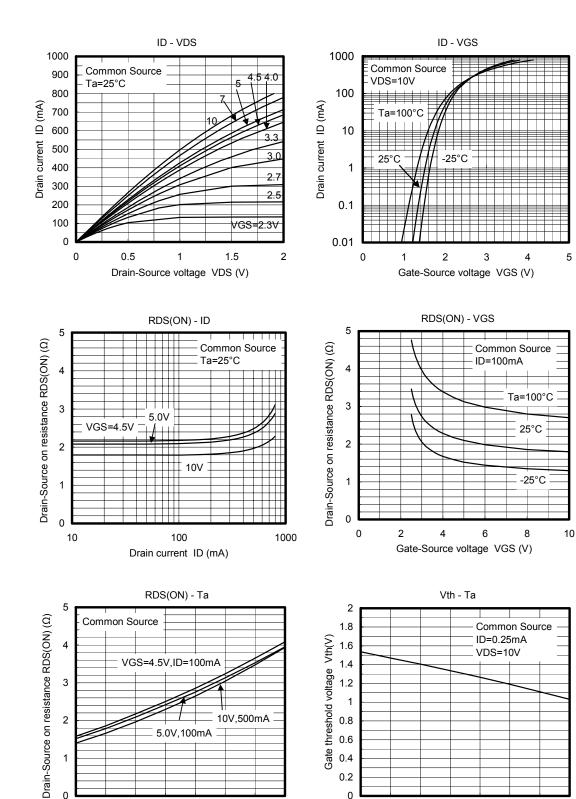
 $V_{th}$  can be expressed as voltage between gate and source when low operating current value is  $I_D$  = 250  $\mu$ A for this product. For normal switching operation,  $V_{GS~(on)}$  requires higher voltage than  $V_{th}$  and  $V_{GS~(off)}$  requires lower voltage than  $V_{th}$ . (Relationship can be established as follows:  $V_{GS~(off)} < V_{th} < V_{GS~(on)}$ )

Please take this into consideration for using the device.  $V_{GS}$  recommended voltage of 4.5 V or higher to turn on this product.

2

-25

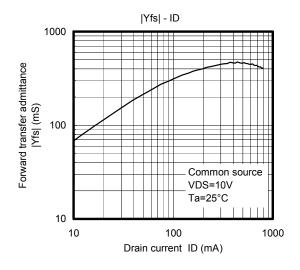
Ambient temperature Ta (°C)

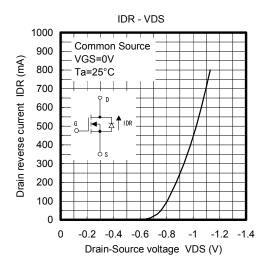


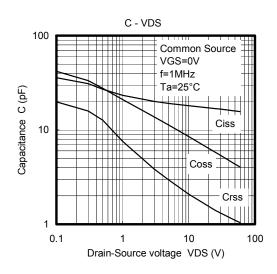
0.6 0.4 0.2 

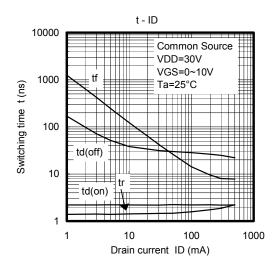
-25

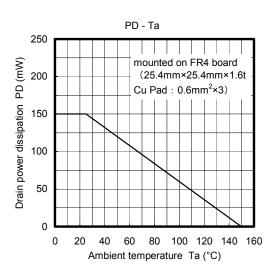
Ambient temperature Ta (°C)











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